Luminescence and Raman Detection of Molecular Cl2 and ClClO Molecules in Amorphous SiO2 Matrix

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ABSTRACT: Chlorine is a common undesirable impurity in synthetic SiO₂ glass for ultraviolet optics and optical fibers. It is usually incorporated into glass as bound Si−Cl groups or interstitial Cl2 molecules. We report a high-sensitivity detection of Cl2 in amorphous $SiO₂$ (a-SiO₂) by photoluminescence (PL) and also by Raman spectroscopy. The Cl₂ PL emission band at 1.22 eV (1016 nm) appears at T < 160 K and shows a characteristic vibronic progression with separations ≈(520–540) cm⁻¹ and an average lifetime of ≈5 ms at 13 K. Its excitation spectrum coincides with the shape of the 3.78 eV (328) nm) optical absorption band of $Cl₂$ in a-SiO₂, corresponding to the X \rightarrow A¹ Π _u transition to repulsive excited state. Direct X \rightarrow a singlet-totriplet excitation was also observed at 2.33 eV (532 nm). Cl₂ PL may serve as a sensitive and selective tool for monitoring Cl impurities and their reactions in a-SiO₂. A Raman band of $Cl₂$ is found

at 546 cm⁻¹. Cl₂ photodissociation at energies up to 4.66 eV (266 nm) was not detected, pointing to a strong cage effect in a-SiO₂ matrix. However, 7.9 eV (157 nm) photolysis of interstitial O₂ molecules gives rise to a Raman band at 954 cm⁻¹, indicating a formation of dichlorine monoxide isomer, ClClO molecule by reaction of O atoms with interstitial Cl2.

INTRODUCTION

Synthetic amorphous SiO2 ("a-SiO2") is widely used in optics, photonics, chemical, nuclear, and space technologies. Although often referred as "high purity", in most cases it contains significant $(10^{15}-10^{18} \text{ cm}^{-3})$ amount of chlorine impurities, left after manufacturing by oxidation of SiCl4, or from usage of Cl2 atmosphere to remove Si−OH impurities in low−OH "dry" silicas. The presence of Cl is detrimental for applications requiring deep-ultraviolet (DUV) and vacuum UV (VUV) transparency, resistance against solarization caused by UV-light and/or stability of optical properties in nuclear or space radiation environments.² a-SiO₂ with improved VUV trans-parency is obtained in chlorine-free processes: sol−gel technique,³ or industrially, by substituting SiCl₄ as a raw material by organic siloxanes, e.g., octamethylcyclotetrasiloxane (OMCTS).⁴ Cl impurities are incorporated mostly as chloride (Si−Cl) groups, where the Si atom is bounded through 3 "bridging" oxygens to the rest of a-SiO₂ network. A smaller fraction of Cl impurities forms interstitial Cl₂ molecules. The presence of excess oxygen in a-SiO2 network increases the relative fraction of Cl2 vs Si−Cl groups, while in the presence of interstitial H2 chlorine tends to form interstitial HCl molecules.⁵

Chlorine impurities in $a-SiO₂$ are hard to monitor by spectroscopic methods. Si−Cl groups have no optical

absorption (OA) bands in the visible-to-DUV range and only cause an additional unstructured absorption near the VUV fundamental absorption edge.¹ Infrared absorption/Raman band of Si−Cl bond stretching mode at ≈620 cm−¹⁶ is typically too weak to be resolved on the background of the fundamental bands. Raman band of $Cl₂$ in SiO₂ has not been reported. However, in contrast to Si-Cl groups, interstitial Cl_2 molecules in a-SiO₂ have a distinct OA band at 3.8 eV (326 nm)¹ corresponding to the X ${}^{1}\Sigma_{g}^{+}$ \rightarrow A ${}^{1}\Pi_{1u}$ band in a free Cl₂ molecule. However, its absorption peak cross section ($\sigma = 2.6 \times 10^{-19}$ cm² for free Cl₂⁷) is low in comparison with other OA bands in irradiated a-SiO2. It is often obscured by the wing of the broad OA band at 4.8 eV (258 nm) due to dangling oxygen bonds; $\frac{8}{3}$ moreover, it can be confused with the OA band at 3.7 eV (335 nm) due to the singletto-triplet transition in a divalent

Ge atom 9 in Ge-doped a-SiO₂.

A weak PL emission in the 1.5 eV ($\approx 800 \text{ nm}$) region showing vibrational structures was found in a-SiO 10 and 2

tentatively assigned to Si O O Si (peroxide linkage) bonding configuration.¹¹ Subsequently it was noted¹² that the reported^{10,11} PL bears resemblance to the PL of $Cl₂$ in inert gas

matrices;¹³ however, it was not further explored. Due the advances in sensitive near-IR light detectors, this spectral region has become more accessible. Here we report detailed properties of the PL of interstitial Cl_2 in a-SiO₂ and show that it can serve as a sensitive tool to monitor the concentration of interstitial $Cl₂$. The Raman signal of interstitial $Cl₂$ is identified as well. It is shown that $Cl₂$ in $SiO₂$ is stabilized against photolysis by the cage effect, and that $Cl₂$ reacts with mobile O atom to form an isomer of dichlorine monoxide, the ClClO molecule.

EXPERIMENTAL SECTION

Three synthetic a-SiO₂ samples denoted S0, S1, and S2, optically polished, sized 5 \times 10 \times 12 mm³, and manufactured by oxidizing SiCl4 in oxygen plasma were investigated. Samples S1 and S2 are distinguished from S0 by >10 times higher concentration of trapped $Cl₂$ molecules, while concentrations of trapped $O₂$ and bound silanol groups in all samples are comparable within a factor of 2 (Table 1). Additionally, S2 was irradiated by F_2 laser (7.9) eV/157 nm, 116 J/cm², T = 300 K). Cl₂ concentrations [Cl₂] were determined from the amplitudes of the $Cl₂$ 3.8 eV (326 nm) optical absorption (OA) band using peak cross section $\sigma = 2.58$ × 10^{-19} cm².⁷ [O₂] was calculated from infrared PL/Raman spectra as described in ref 5. [Si− OH] was obtained from the 3700 cm−¹ infrared OA band using

 $\sigma = 3.14 \times 10^{-19}$ cm².¹⁴ For each species, the accuracy of the relative concentrations (concentration ratios) is ±5%, while the absolute concentrations are less accurate $(\pm 25\%)$ due to uncertainties in the respective calibration coefficients. $5,7,14$

The optical absorption was measured at $T = 295$ K (Hitachi U4000), the PL and PL excitation (PLE) spectra and PL decay kinetics were measured in the T range 14−300 K in a He refrigerator cryostat (Leybold RDK 10−320). PL was excited at several wavelengths by diode-pumped solid state lasers with photon energies (wavelengths) 2.33 eV (532 nm), 2.62 eV (473 nm), and 4.66 eV (266 nm); by a GaN diode laser (3.31 eV/374 nm); and by a N_2 gas laser (3.68 eV/337 nm). The PL and Raman spectra were recorded by 300 mm Andor Shamrock spectrograph (150 L/mm grating PL, 1200 L/mm Raman) and cooled CCD camera (Andor DU971N-UVB). The artifacts, caused by interference fringes (etaloning) in the back-illuminated CCD in the near IR spectral region were removed by calibrating against the spectrum of a standard tungsten lamp. The PL spectral resolution was 5 meV in the 1.2−1.7 eV region. PLE spectra were measured using a 150 W Xe-lamp filtered by 200 mm double monochromator (AMKO LTI). The wave-length-dependence of the excitation intensity was measured by comparing to standard deuterium lamp (Ocean Optics DH-2000-CAL). PL kinetics was obtained by mechanically chopping the excitation light and recording the integral PL signal between 1.55 and 2.1 eV with photomultiplier (Hamamatsu R955) and multichannel photon counter. Decay curve fitting was done using MATLAB optimization toolbox.

Raman spectra were collected with a purpose-built system in the common backscattering geometry, using Nd:YAG laser

(LSR532H, λ = 532.09 nm, 400 mW), a condenser with antireflection coated f/1.6 silica lenses, a laser line cleanup filter, a dichroic 45° mirror, and a long pass edge filter (Semrock LL01-532, LPD01-532, and LP03-532, respectively). Spectral resolution was 6 cm⁻¹ (full width at half-maximum, fwhm), wavenumber accuracy 1 cm⁻¹. The purpose of the measure-ment was to obtain minor $(\approx 0.1\%)$ differences in Raman spectra of samples S2 and S0 with different C_1 concentrations. This level of accuracy requires: (i) a low noise level, (ii) a low intensity drift, and (iii) an absence of CCD-related small artifacts ("built-in" pixel noise). To accomplish this: (i) 600 nearly full-scale 16 bit spectra were averaged at each measurement $(\approx 1.7 \times 10^{7}$ ADC counts per pixel bin), (ii) three pairs of thus averaged spectra were taken alternatively reinserting samples S0 and S2 to check the intensity drift and repeatability, and (iii) an additional three pairs of similarly averaged spectra were measured with the spectrograph center point shifted by 1.5 nm to verify that the influence of CCD pixel nonuniformity was negligible.

E RESULTS

The PL emission spectra of Cl-containing $a-SiO₂$ sample S1 are shown in Figure 1. A broad luminescence emerges at

Figure 1. Photoluminescence spectra of Cl₂-containing amorphous $SiO₂$ (sample S1) measured at 3.31 eV (374 nm) CW laser excitation (2 mW) at temperatures between 13 and 160 K. Inset shows the temperature dependence of intensity, integrated over the 1.2−1.8 eV (1033 nm-689 nm) region. Numbering of sub-bands indicates the ground state vibrational level quantum numbers v of $Cl₂$ molecule.

temperatures $T < 160$ K. Distinct vibronic structures develop at $T < 110$ K, showing series of narrow sub-bands with fwhm ≈ 30 meV and separations decreasing from 65 meV at 1.8 eV to 58 meV at 1.2 eV. The smaller structures visible in some subbands are artifacts due to incompletely corrected etaloning of CCD.

A Gaussian fit to the broad-band component of PL yields peak at 1.22 eV (1016 nm) and fwhm of 0.42 eV. This PL was observed at all discrete laser photon energies used (2.33, 2.62, 3.31, 3.68, 4.66 eV). The excitation peak is at 3.80 eV (326 nm) with fwhm =0.6 eV (Figure 2B); it nearly coincides with the

Figure 2. (A) Optical absorption spectrum, measured at 295 K (sample S2, before irradiation). The feature marked by an asterisk is an instrument artifact. (B) Photoluminescence excitation spectrum, (sample S1, $T = 14$ K, resolution 0.05 eV). The inset shows potential energy curves for the ground (X) and the lowest excited states (a and A) of Cl2 molecule, calculated in ref 15; arrows indicate the observed excitation and luminescence transitions.

absorption spectrum (Figure 2A). The emission spectra taken using different energies within this excitation band preserved the same form; no peak shifts could be detected. The intensity of the 1.22 eV PL band under UV laser excitation (3.31 eV, 4.66 eV) remained constant (±1%) under prolonged (1 h) irradiation, photobleaching was not detected.

High-intensity (50 mW) excitation at photon energy 2.32 eV, much below the energies of the PLE band of Figure 2, produced a weak infrared PL band, overlapped by the wing of the PL band due to oxygen dangling bonds "non-bridging oxygen hole centers" (NBOHC) 16 (Figure 3). It shows the same characteristic vibronic structure as present in Figure 1.

Figure 3. Infrared luminescence of Cl2 molecules in SiO2 (sample S1) under direct excitation to the radiative 3 $\Pi_{\rm u}$ state (see the inset to Figure 2), overlapped by a wing of 1.9 eV PL band due to oxygen dangling bonds (NBOHC's).

The PL decay kinetics (Figure 4) deviates from the singleexponent law when measured over dynamic range of 3 decades. At least 3 exponents with different decay constants τ_i had to be included in the nonlinear least-squares fit $I(t) = \sum_{i=1}^{3} C_i \exp(-t/\tau_i)$ to obtain a fair agreement with the data. The quality of the fit was not improved by inclusion of additional exponents. Fitting with a stretched exponent function $I(t) =$

 $\text{Ce}^{-\left[\text{t}+\text{t}/\text{T}\right]_\beta}$ gave significantly worse results. An excellent fit to kinetics, measured at 13 K (Figure 4, top curve) was obtained with decay constants 3.04, 7.28, and 16.67 ms (Figure 4, red line). Their relative contributions $\tau_i \times C_i$ to the total intensity

Figure 4. Luminescence decay kinetics measured for the spectral range 1.55−1.7 eV (800−729 nm) at temperatures between $T = 13$ and 140 K with 2.62 eV (473 nm) excitation (sample S1). The smooth red line shows a three-exponent fit to the kinetics at $T = 13$ K. Inset shows the temperature dependences of the normalized luminescence intensity (filled circles) and of the average decay constant τ, obtained by leastsquares fitting to a single exponent (hollow squares).

were 34.4%. 50.3%, and 15.3%, respectively. While obviously not unique, this fit gives a rough outline of the underlying, probably continuous, distribution of τ. The T-dependence of the "average" τ was estimated, using a nonlinear fit with a single exponent. The average τ is \approx 5.2 ms at 13 K; it decreases to 0.6 ms at 140 K (Figure 4, inset). The τ value at 20 K is 5 ms, \approx 2.5 times larger than previously reported.¹⁰

The Figure 5 bottom trace shows the nearly coinciding Raman spectra of "low-Cl₂" sample S0 and "high-Cl₂" F₂-laser

Figure 5. Raman spectra of Cl₂ and ClClO molecules in amorphous SiO2. Bottom trace(s): two overlapping Raman spectra of the "low- $Cl₂$ ", unirradiated sample S0, and of the "high- $Cl₂$ ", $F₂$ -laser-irradiated sample S2. Top trace: the difference spectrum S2 − S0 (×500). Peaks due to interstitial $Cl₂$, ClClO and $O₂$ molecules are marked by arrows. Peaks marked by asterisks may be subtraction-induced artifacts; their spectral positions were unstable against small deviations in the intensity of S0 relative to S2.

irradiated sample S2. They have the usual shape of the fundamental Raman spectrum of $a-SiO₂$. Top trace shows the difference spectrum S2 − S0 multiplied by 500, obtained as average of six pairs of sequentially measured spectra of samples S0, S2 (see the Experimental Section). The difference spectra, obtained individually from each of these 6 pairs showed moderately fluctuating baselines, caused by slight admixture of fundamental Raman spectrum due to intensity drifts or sample reinsertion inaccuracies. This introduced fluctuations in spectral positions of several peaks in the difference spectrum, marked by "*" in Figure 5. In contrast, the spectral positions of 3 peaks

located at 546.2, 953.5, and 1549.6 cm^{-1} were not significantly affected by these inaccuracies and may be considered as reliable.

■ DISCUSSION

Luminescence of Cl2. A comparison of the characteristic shape of the PL emission band in Figure 1 with the triplet-tosinglet a ${}^{3}\Pi_{u} \rightarrow X \ {}^{1}\Sigma_{g}^{+}$ emission reported for matrix-isolated Cl₂ molecules in Ar, Kr, and Xe cryo-crystals^{13,17,18} leaves little doubt that the "1.22 eV" PL band is due to interstitial Cl2 molecules in SiO2. This assignment is further corroborated by similar, milliseconds-range PL lifetimes: between 3 to 15 ms in our work (Figure 4) and 83, 76, and 55 ms in Ne, Ar and Kr cryocrystals, respectively.¹⁷ The vibronic lines of Cl₂ PL in Ar crystals are much sharper than in a-SiO2, and separate vibronic progressions for three different naturally occurring isotopic compositions of Cl₂: 35 Cl−³⁵Cl (57.4%), 35 Cl−³⁷Cl (36.7%), and 37 Cl− 37 Cl (5.9%) are observed. 13 If the positions of "isotope-averaged" vibronic PL lines of $Cl₂$ in Ar are calculated as weighed average of the reported 13 vibronic line positions of these $\overline{3}$ Cl₂ isotopologues, then they coincide with those of the vibronic peaks between 1.9 and 1.3 eV in Figure 1 very well. The deviations (4 meV) were less than the spectral resolution (5 meV). The separations of adjacent vibronic peaks in Figure 1 decrease linearly with the quantum number, with a slope of (0.76 ± 0.06) meV (6.2 ± 0.5 cm⁻¹), which yields the anharmonicity parameter ω x = (3.1 ± 0.25) cm⁻¹ in the standard Morse potential model describing the dependence of emission energy $E(v)$ on excited state zero-phonon ($v' = 0$) energy E_0 , ground state vibrational quantum number v, harmonic vibrational frequency ω (in cm⁻¹ units), and anharmonicity parameter ωχ:

$$
E(v) = E_0 - hc(\omega(v(1/2)) - \omega \chi(v + (1/2)^2 \quad (1)
$$

This ω **x** value (3.1 cm⁻¹) is close to its reported values for Cl₂ in Ar (2.73 cm⁻¹) or Kr (2.77 cm⁻¹) matrices.¹⁷ E(0) – E(1) is given independently by 546.2 cm⁻¹ Cl₂ line in the Raman spectrum (see below). Then the harmonic frequency ω $= 546.2$ cm⁻¹ + 2ωχ = 552.4 cm⁻¹, and the PL spectrum is best fitted with $E_0 = 17008$ cm⁻¹. This predicts "isotope-weighted" zero-phonon transition energy ≈2.074 eV and allows an assignment of vibrational numbers v to the subbands in PL spectrum (Figure 1). It coincides with the ν assignments

made for PL bands of Cl₂ in the Ar matrix.^{13,17}

The peak position (3.78 eV) and fwhm (0.67 eV) of the absorption band (Figure 2A) coincide well with those reported previously for Cl₂ in $SiO_2^{1'}$ and for free Cl₂ molecules (3.762) and 0.68 eV, respectively).⁷ The PLE spectrum nearly exactly coincides with the absorption spectrum, the slightly smaller half-width $(\approx 0.6 \text{ eV})$ can be attributed to the difference between the measurement temperatures of PLE ($T = 14$ K) and OA ($T = 295$ K) spectra. As far as we know, a-SiO₂ is the only oxide material for which matrix-isolated luminescence of Cl2 has been reported. The intensity of the PL in our sample with $\frac{1}{7}$ \times 10¹⁷ Cl₂/cm³ allows one to estimate that <10¹⁴ Cl₂/cm³ in mm-sized samples and $\langle 10^{12} \text{ Cl}_2/\text{cm}^3$ in optical fibers could be easily detected.

The 3.78 eV OA and PLE band of Cl_2 is due to the transition from the ground state $X \binom{1}{2}$ to $A \binom{1}{1}$. The emission occurs from the lowest triplet state $a_2^3 \overline{\Pi}_{u}$. The potential energy curves calculated for these states¹⁵ and absorption-emission transitions observed in the present work are shown in Figure 2, inset. A

more detailed term scheme, which takes into account the spin– orbital coupling in 3 Π _u state, is calculated in ref 19.

In a free Cl₂ molecule, the ${}^{1}\Pi_{\text{u}}$ excited state is repulsive, with energy above the dissociation energy (2.5 eV) (Figure 2, see ref 20 for an overview of Cl_2 properties). Evidently, in a-SiO₂ matrix, the Cl atoms are held together by the "cage effect" and PL occurs after relaxation to the lowest triplet manifold 3 Π_{u} . For Cl₂ in inert gas crystals, the cage effect is very strong in Ar, smaller in Kr, and weak in Xe cryocrystals.^{21,22} While Cl₂ in Xe is dissociated by excitation in the 3.78 eV OA band, 21 in the case of Ar matrix the threshold of efficient dissociation is 9.2 eV with a weaker threshold at 6.2 eV^{22} The decrease of cage effect in the row of Ar \rightarrow Kr \rightarrow Xe crystals correlates with an increase of the respective lattice constants (526, 571, and 620 pm, respectively) of their fcc cubic structures.

In the case of a-SiO₂, photobleaching of Cl_2 PL was not observed at any excitation photon energy within the 2.33−4.66 eV range, used in this study. Taking into account the power density of the focused laser beam, the irradiation duration and the published¹ $Cl₂$ absorption cross section, we estimated that the permanent dissociation probability of Cl_2 molecule on absorbing of 4.66 eV photon was <1% at $T = 13$ K. The average diameter of interstitial voids in the structure of a-SiO₂ is around 400−500 pm, as estimated from positron annihilation²³ or reverse Monte Carlo simulation studies.²⁴ The largest sites may accommodate a Cl_2 molecule (Cl−Cl distance, 199 pm; transversal van der Waals diameter, 380 pm^{25}). The absence of photobleaching indicates that neighboring sites, appropriate for stabilizing the separated Cl atom, are not easily reached. Neutral interstitial Cl atoms $(Cl⁰)$ have been detected by electron paramagnetic resonance in Clcontaining a-SiO₂ only after a much higher energy (100 keV Xrays) excitation.²⁶ It is suggested that Cl^0 is responsible for absorption bands in X-ray irradiated $SiO₂$ -core optical fibers at 3.5 eV^{27} and for *v*-ray-induced absorption of optical fibers in the nearinfrared

 $_{2,28}$ region.

The optical absorption cross section spectrum⁷ and

calculations indicate that absorption at 15,19 photon energies \sim 2.5 eV is due to the spin-forbidden X ${}^{1}\Sigma_{g}^{+}$ → a ${}^{3}\Pi_{u}$

transition (Figure 2, inset). The weak PL of interstitial Cl2 in a-SiO2, detected under 2.33 eV laser light (Figure 3), evidently is excited via this transition.

Raman Signals of Cl2 and ClClO. Out of the three reliably measured Raman peaks, marked by arrows in difference spectrum in Figure 5, the peak at 1549.6 cm⁻¹ is easily identified as due to interstitial O_2 molecules in SiO_2 . Its closeness to the exactly measured value of 1548.5 cm⁻¹²⁹ gives an additional confidence that positions of the other two, unassigned peaks are accurate within ± 1 cm⁻¹. The strongest of them, located at 546.2 cm⁻¹, can be assigned to an interstitial Cl_2 in a-SiO₂ because: (i) it is larger in the sample S2 with

larger Cl₂ concentration (Table 1), and (ii) its position is very close to ($v =$ 0) → ($v = 1$) energy for the ³⁵Cl -³⁵Cl in gas

 (554.3 cm^{-1}) or in Ar matrix (549.2 cm^{-1}) .¹⁷ Additionally, as discussed above, using this Raman band energy in Morse-potential vibrational energy calculation eq 1 yields the same assignments of vibrational quantum numbers as for Cl₂ in Ar matrix.

The sharp Raman peak at 953.5 cm^{-1} in difference spectrum (Figure 5) has not been previously reported in SiO2. It is likely related to the difference in Cl concentrations in samples S2 and S0. Similar peak in UV resonance Raman spectra at 954 cm−¹ has been assigned to Cl−O stretch in ClClO molecules

dissolved in CCl $_4$.³⁰ ClClO molecules in Ar matrix give rise to IR absorption bands at 961.7 cm^{-1} (Cl-³⁵Cl-O) or 953.4 cm^{-1} (Cl -^{37} Cl–O).³¹ On the other hand, it is well-known that O_2 in a-SiO₂ is less constrained by cage-effect, and that F₂-laser photolysis creates mobile O atoms.³² Evidently, a reaction

$$
Cl 2 + O \rightarrow ClClO
$$
 (2)

takes place. Dichlorine monoxide is the largest interstitial 3 atom species detected until now in a-SiO2: interstitial ozone O_3 ,³² water H₂O, hydroperoxy radical HO₂^{•33} and chlorine dioxide $CIO₂$, 34 only 4-atom chlorate radical $CIO₃$ ^{\bullet 34} is larger. Our present Raman data (Figure 5) do not confirm a creation of another isomer of dichlorine monoxide, Cl−O−Cl. It should show Raman band due to the symmetric stretch mode around 640 cm⁻¹;^{31,35} however, the 640 cm⁻¹ peak, marked by an asterisk in Figure 5, was not consistently present in all difference spectra (Results), and thus cannot be confirmed on the basis of the present data.

The formation of dichlorine monoxide in $a-SiO₂$ may be of practical importance. Reaction 2 may deplete the concentration of interstitial O_2 in O_2 -loaded a-Si O_2 optical fibers, suggested as radioluminescent detectors for dosimetric applications.³⁶ The creation of ClClO can strongly affect optical elements and fibers for UV region, where $a-SiO₂$ is the usual material of

choice. The OA cross section σ of ClClO is large (1.3 × 10⁻¹⁷ cm² at 260 nm³¹); it is ≈100 times larger than σ for the UV OA band of free $Cl₂$ molecule.⁷ Therefore, the formation of ClClO may be an important and so far not considered mechanism contributing to the well-known detrimental effect of chlorine impurities on UV optical transmission of a-SiO2.

CONCLUSIONS

With the proliferation of near-infrared-sensitive Si detectors, the luminescence of interstitial Cl_2 molecules in amorphous SiO_2 has become easy to observe. It provides sensitive and highly specific spectral signature, suitable for monitoring of molecular chlorine, and its chemical and photoinduced reactions in amorphous $SiO₂$. In this work, detailed character-istics of this luminescence were obtained. Additionally, the Raman signal of Cl_2 in SiO_2 was observed for the first time. Cl_2 molecule in amorphous SiO_2 is stabilized by a strong cage effect, preventing its photodissociation by photons with energy \leq eV. However, Cl₂ can accept in its cage an additional atomic oxygen created by photolysis of interstitial $O₂$ and form ClClO molecule. This molecule is a strong ultraviolet absorber and suppression of its formation may be important for irradiation-and solarization-resistant SiO2-based UV optics.

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